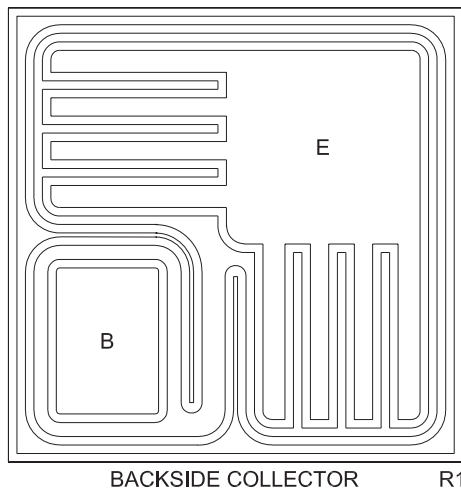


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 X 80 MILS
Die Thickness	8 MILS
Base Bonding Pad Area	18 X 27 MILS
Emitter Bonding Pad Area	34 X 34 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Pd/Ag (20,000Å)

Geometry



GROSS DIE PER 4 INCH WAFER

1,445

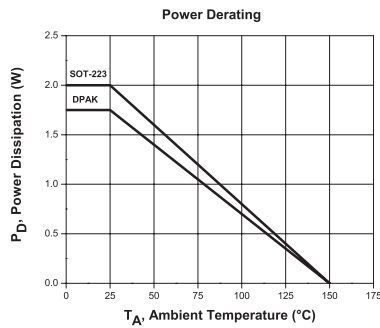
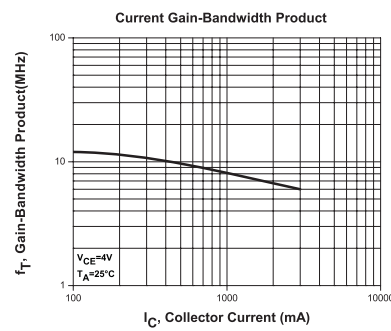
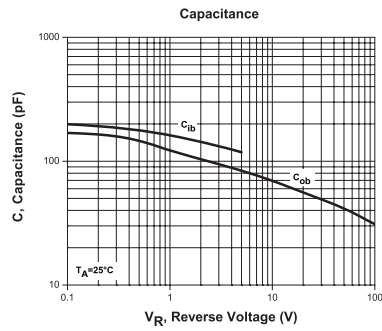
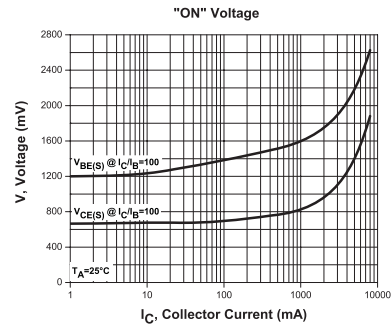
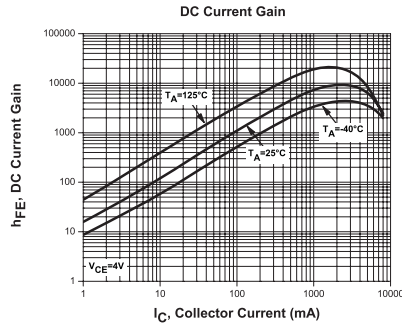
PRINCIPAL DEVICE TYPES

CZT127

CJD127

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